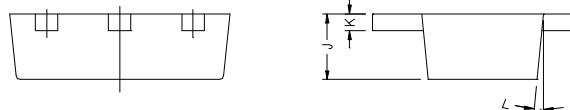
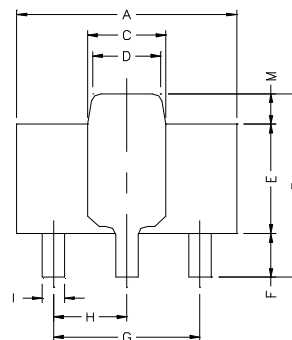


RoHS Compliant Product

**SOT-89**



**Features**

Designed for general purpose application requiring high breakdown voltage.



- 1.BASE
- 2.COLLECTOR
- 3.EMITTER

Marking: 5551  
XXXX  
(xxxx = Date Code)

REF.	Min.	Max.	REF.	Min.	Max.
A	4.4	4.6	G	3.00	REF.
B	4.05	4.25	H	1.50	REF.
C	1.50	1.70	I	0.40	0.52
D	1.30	1.50	J	1.40	1.60
E	2.40	2.60	K	0.35	0.41
F	0.89	1.20	L	5° TYP.	
			M	0.70 REF.	

**ABSOLUTE MAXIMUM RATINGS (Tamb=25°C, unless otherwise specified)**

Parameter	Symbol	Value	Unit
Collector-Base Voltage	$V_{CBO}$	180	V
Collector-Emitter Voltage	$V_{CEO}$	160	V
Emitter-Base Voltage	$V_{EBO}$	6	V
Collector Current	$I_C$	600	mA
Total Power Dissipation	$P_D$	1.2	W
Operating Junction and Storage Temperature	$T_J, T_{STG}$	-55 ~ +150	°C

**ELECTRICAL CHARACTERISTICS (Tamb=25°C)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Collector-Base Breakdown Voltage	$BV_{CBO}$	180	-	-	V	$I_C = 100\mu A$
Collector-Emitter Breakdown Voltage	$BV_{CEO}$	160	-	-	V	$I_C = 1mA$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	6	-	-	V	$I_E = 10\mu A$
Collector Cut-off Current	$I_{CBO}$	-	-	50	nA	$V_{CB} = 120V$
Emitter Cut-off Current	$I_{EBO}$	-	-	50	nA	$V_{EB} = 4V$
Collector-Emitter Saturation Voltage	$V_{CE(sat)1}$	-	-	150	mV	$I_C = 10mA, I_B = 1mA$
	$V_{CE(sat)2}$	-	-	200	mV	$I_C = 50mA, I_B = 5mA$
Output Capacitance	$C_{ob}$	-	-	6	pF	$V_{CB} = 10V, f = 1MHz$
Base-Emitter Voltage	$V_{BE(sat)1}$	-	-	1	V	$I_C = 10mA, I_B = 1mA$
	$V_{BE(sat)2}$	-	-	1	V	$I_C = 50mA, I_B = 5mA$
DC Current Gain	$h_{FE1}$	80	-	-		$V_{CE} = 5V, I_C = 1mA$
	$h_{FE2}$	80	-	250		$V_{CE} = 5V, I_C = 10mA$
	$h_{FE3}$	30	-	-		$V_{CE} = 5V, I_C = 50mA$
Transition Frequency	$f_T$	100	-	300	MHz	$V_{CE} = 10V, I_C = 10mA, f = 100MHz$

**Characteristics Curve**

